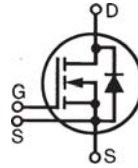


# HiPerFET™

## Power MOSFET

### Single MOSFET Die

# IXFN39N90

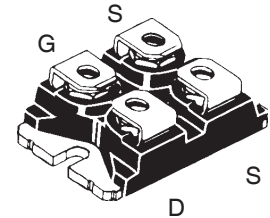


N-Channel Enhancement Mode  
Avalanche Rated

$V_{DSS} = 900V$   
 $I_{D25} = 39A$   
 $R_{DS(on)} \leq 220m\Omega$   
 $t_{rr} \leq 250ns$

miniBLOC, SOT-227  
 E153432

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	900	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	900	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$	39	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	154	A
$I_A$	$T_C = 25^\circ C$	39	A
$E_{AS}$	$T_C = 25^\circ C$	4	J
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	5	V/ns
$P_D$	$T_C = 25^\circ C$	694	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$V_{ISOL}$	50/60 Hz, RMS $t = 1$ minute $I_{ISOL} \leq 1mA$ $t = 1$ second	2500 3000	V~ V~
$M_d$	Mounting Torque Terminal Connection Torque	1.5/13 1.3/11.5	Nm/lb.in. Nm/lb.in.
<b>Weight</b>		30	g



G = Gate      D = Drain  
S = Source

Either Source Terminal at miniBLOC can be used as Main or Kelvin Source.

### Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low Package Inductance

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- DC Choppers
- Temperature and Lighting Controls

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{DSS}$	$V_{GS} = 0V$ , $I_D = 3mA$	900		V
$BV_{DSS}$	<b>Temperature Dependence</b>		3.68	V/K
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8mA$	3.0		5.5 V
$V_{GS(th)}$	<b>Temperature Dependence</b>		-0.009	V/K
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			100 $\mu A$ 2 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			220 m $\Omega$

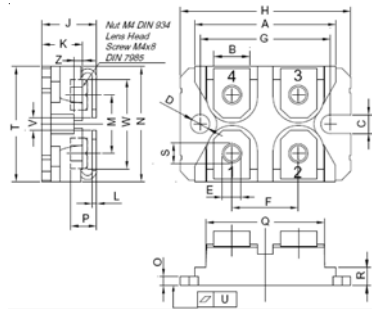
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 15\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1	30	45	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		9200	pF
$C_{oss}$			1360	pF
$C_{rss}$			380	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		45	ns
$t_r$			68	ns
$t_{d(off)}$			125	ns
$t_f$			30	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		390	nC
$Q_{gs}$			65	nC
$Q_{gd}$			190	nC
$R_{thJC}$			0.18	$^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			39 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			154 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.3 V
$t_{rr}$	$I_F = 39\text{A}$ , $-di/dt = -100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$ , $V_{GS} = 0\text{V}$			250 ns
$Q_{RM}$			2.0	$\mu\text{C}$
$I_{RM}$			9.0	A

Note 1: Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

### SOT-227B miniBLOC (IXFN)



(M4 screws (4x) supplied)

Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Figure 1. Output Characteristics at 25°C

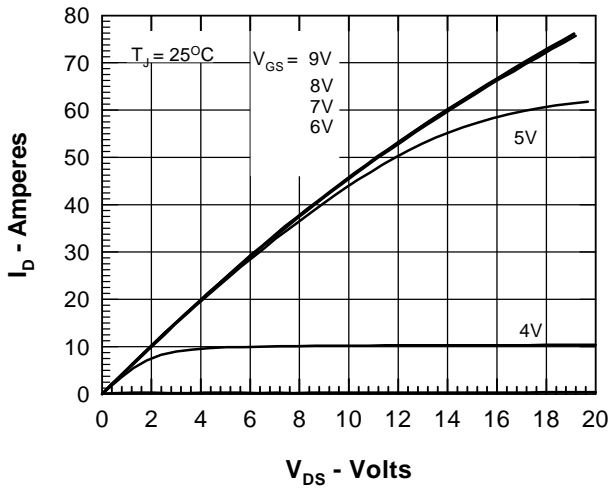


Figure 2. Output Characteristics at 125°C

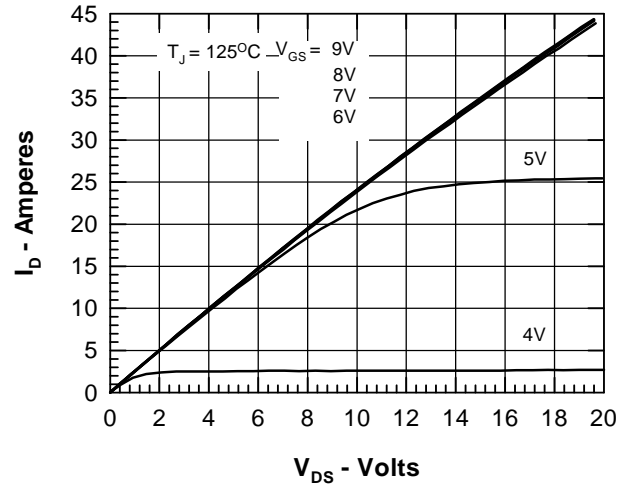


Figure 3.  $R_{DS(on)}$  normalized to 0.5  $I_{D25}$  value vs.  $I_D$

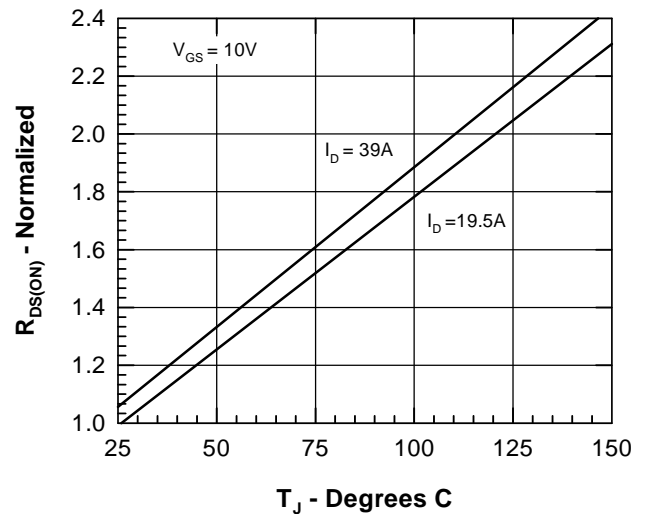
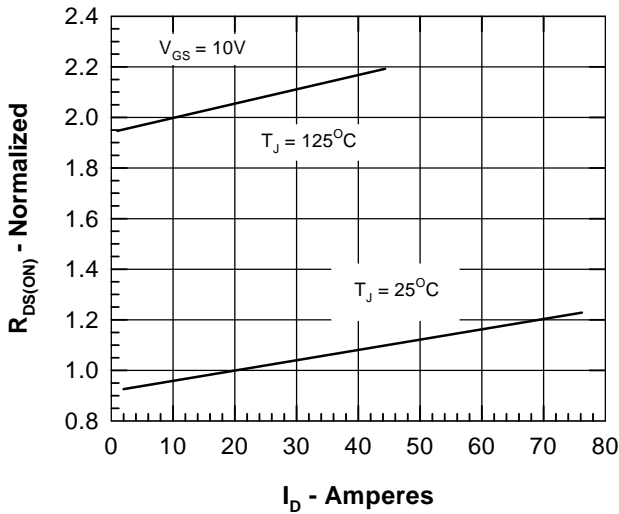


Figure 5. Drain Current vs. Case Temperature

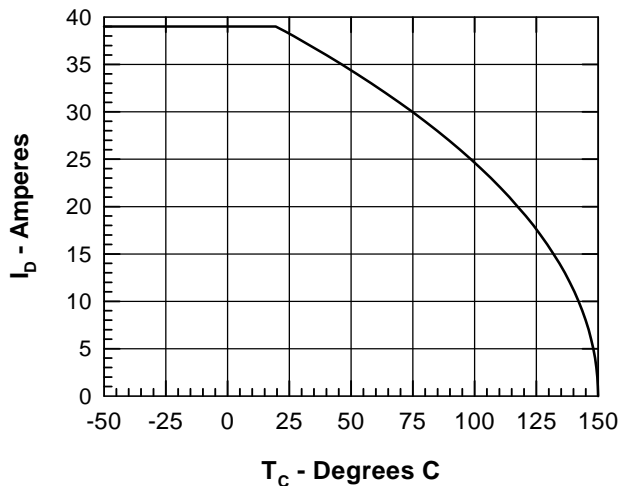


Figure 6. Admittance Curves

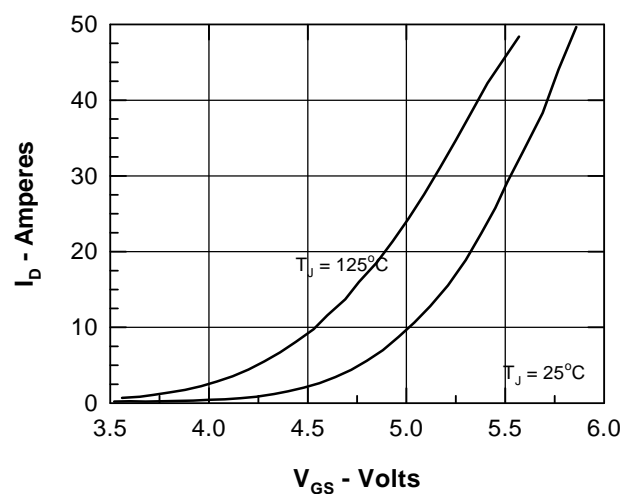


Figure 7. Gate Charge

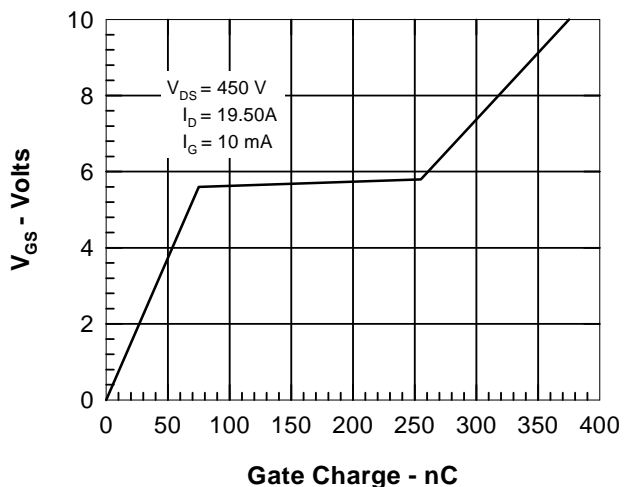


Figure 8. Capacitance Curves

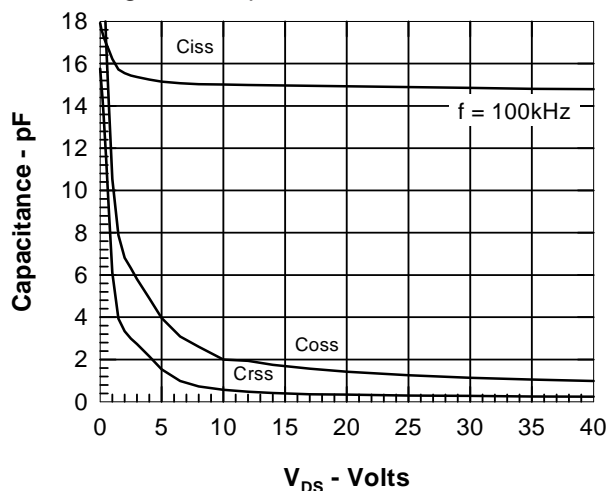


Figure 9. Forward Voltage Drop of the Intrinsic Diode

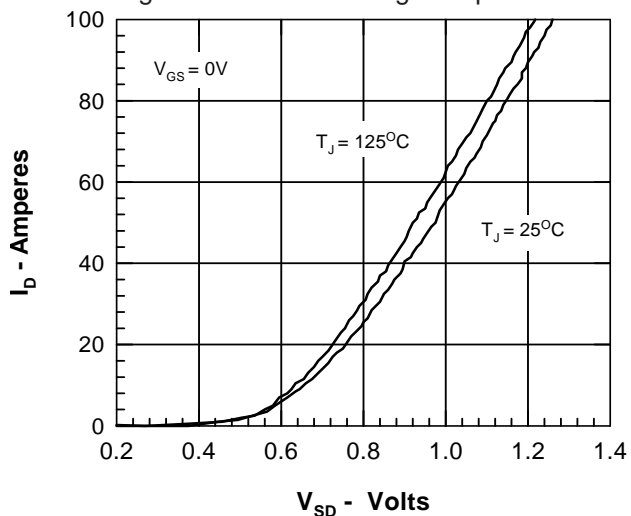


Figure 10. Transient Thermal Resistance

